High Speed, Four Channel MOSFET Driver with Non-Inverting Outputs

Features

- Non-inverting, four channel MOSFET driver
- 6.0ns rise and fall time
- ▶ 2.0A peak output source/sink current
- ▶ 1.8 to 5.0V input CMOS compatible
- ▶ 5.0 to 10V total supply voltage
- Smart logic threshold
- Low jitter design
- ▶ Four matched channels
- Drives two P- and two N-channel MOSFETs
- Outputs can swing below ground
- Low inductance quad flat no-lead package
- High performance, thermally-enhanced package

Applications

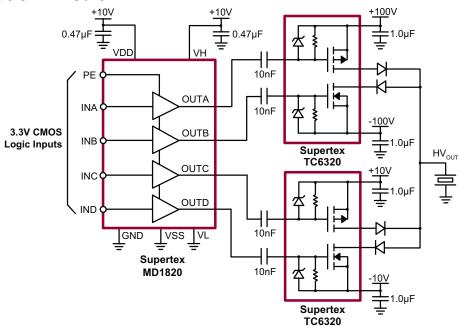
- Medical ultrasound imaging
- Piezoelectric transducer drivers
- Nondestructive evaluation
- PIN diode driver
- ► CCD Clock driver/buffer
- High speed level translator

General Description

The Supertex MD1820 is a high speed, four channel MOSFET driver designed to drive high voltage P- and N-channel MOSFETs for medical ultrasound applications and other applications requiring a high output current for a capacitive load. The high-speed input stage of the MD1820 can operate from a 1.8 to 5.0V logic interface with an optimum operating input signal range of 1.8 to 3.3V. An adaptive threshold circuit is used to set the level translator switch threshold to the average of the input logic 0 and logic 1 levels. The input logic levels may be ground-referenced, even though the driver is putting out bipolar signals. The level translator uses a proprietary circuit, which provides DC coupling together with high-speed operation.

The output stage of the MD1820 has separate power connections enabling the output signal L and H levels to be chosen independently from the supply voltages used for the majority of the circuit. As an example, the input logic levels may be 0 and 1.8V, the control logic may be powered by +5.0 and -5.0V, and the output L and H levels may be varied anywhere over the range of -5.0 to +5.0V. The output stage is capable of peak currents of up to ±2.0A, depending on the supply voltages used and load capacitance present. The PE pin serves a dual purpose. First, its logic H level is used to compute the threshold voltage level for the channel input level translators. Second, when PE is low, the outputs are HiZ. This assists in properly precharging the AC coupling capacitors that may be used in series in the gate drive circuit of an external PMOS and NMOS transistor pair.

Typical Application Circuit



Ordering Information

Device	16-Lead QFN 3.00x3.00mm body 1.00mm height (max) 0.50mm pitch
MD1820	MD1820K6-G

⁻G indicates package is RoHS compliant ('Green')

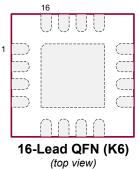
Absolute Maximum Ratings

Parameter	Value
V _{DD} -V _{SS} , Logic supply voltage	-0.5V to +12.5V
V _H , Output high supply voltage	V_{L} - 0.5V to V_{DD} +0.5V
V _L , Output low supply voltage	V_{SS} - 0.5V to V_H + 0.5V
V _{ss} , Low side supply voltage	-6.0V to +0.5V
Logic input levels	V _{ss} - 0.5V to GND +5.5V
Maximum junction temperature	+125°C
Storage temperature	-65°C to 150°C
Operating temperature	-20°C to +85°C
Package power dissipation	2.2W
Thermal resistance $(\theta_{JA})^*$	55°C/W

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.



Pin Configuration



Product Marking



Y = Last Digit of Year Sealed W = Code for Week Sealed L = Lot Number

___ = "Green" Packaging

Package may or may not include the following marks: Si or §

16-Lead QFN (K6)

DC Electrical Characteristics ($V_H = V_{DD} = 10V$, $V_L = V_{SS} = GND = 0V$, $V_{PE} = 3.3V$, $T_A = 25$ °C)

Sym	Parameter	Min	Тур	Max	Units	Conditions
V _{DD} - V _{SS}	Logic supply voltage	4.75	-	11.5	V	4.0V ≤ V _{DD} ≤11.5V
V_{ss}	Low side supply voltage	-5.5	-	0	V	
$V_{\rm H}$	Output high supply voltage	V _{ss} +2.0	-	V _{DD}	V	
V_{L}	Output low supply voltage	V _{ss}	-	V _{DD} -4.0	V	
l _{DDQ}	V _{DD} quiescent current	-	60	-	μA	No input transitions, PE = 0
I _{HQ}	V _H quiescent current	-	2.0	-	μA	No input transitions, FE = 0
l _{DDQ}	V _{DD} quiescent current	-	0.8	-	mA	No input transitions, PE = 1
l _{HQ}	V _H quiescent current	-	2.0	-	μA	No input transitions, FE = 1
l _{DD}	V _{DD} average current	-	3.5	-	mA	One channel on at 5.0Mhz,
I _H	V _H average current	-	10	-	mA	No load
V _{IH}	Input logic voltage high	V _{PE} -0.3	-	V_{PE}	V	
V _{IL}	Input logic voltage low	0	-	0.3	V	For logic inputs INA, INB, INC,
I _{IH}	Input logic current high	-		1.0	μA	and IND
I	Input logic current low	-	-	1.0	μA	
V _{IH}	PE input logic voltage high	1.70	3.30	5.25	V	
V _{IL}	PE input logic voltage low	0	-	0.3	V	For logic input PE
R _{IN_PE}	PE input impedance to GND	100	-	-	ΚΩ	

^{* 1.0}oz 4-layer 3x4" PCB

DC Electrical Characteristics (cont.) $(V_H = V_{DD} = 10V, V_L = V_{SS} = GND = 0V, V_{PE} = 3.3V, T_A = 25^{\circ}C)$

Sym	Parameter	Min	Тур	Max	Units	Conditions
C _{IN}	Logic input capacitance	-	5.0	10	pF	
R _{SINK}	Output sink resistance	-	1.5	-	Ω	I _{SINK} = 50mA
R _{SOURCE}	Output source resistance	-	2.0	-	Ω	I _{SOURCE} = 50mA
I _{SINK}	Peak output sink current	-	2.0	-	Α	
SOURCE	Peak output source current	-	2.0	-	Α	

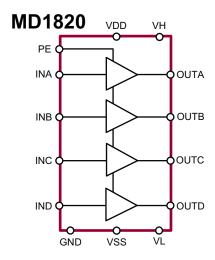
AC Electrical Characteristics $(V_H = V_{DD} = 10V, V_L = V_{SS} = GND = 0V, V_{PE} = 3.3V, T_A = 25^{\circ}C)$

Sym	Parameter	Min	Тур	Max	Units	Conditions
t _{irf}	Input or PE rise & fall time	-	-	10	ns	Logic input edge speed requirement
t _{PLH}	Propagation delay when output is from low to high	-	6.5	-	ns	C _{LOAD} = 1000pF, see timing
t _{PHL}	Propagation delay when output is from high to low	-	6.5	-	ns	diagram
t _r	Output rise time	-	7.0	-	ns	Input signal rise/fall time 2.0ns
t _f	Output fall time	-	7.0	-	ns	
lt _r -t _f l	Rise and fall time matching	-	1.0	-	ns	
I t _{PLH} -t _{PHL} I	Propagation low to high and high to low matching	-	1.0	-	ns	For each channel
$\Delta t_{\sf dm}$	Propagation delay matching	-	±2.0	-	ns	Device to device delay match
t _{PE-ON}	PE on-time	-	-	5.0	μs	V _{PE} = 1.7 ~ 5.25V V _{DD} = 7.5 ~ 11.5V
t _{PE-OFF}	PE off-time	-	-	4.0	μs	-20 ~ 85°C

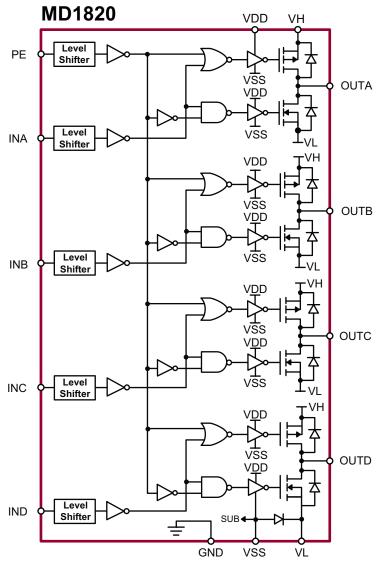
Logic Truth Table

Logic	Logic Inputs					
PE	Output					
Н	L	V _L				
Н	Н	V _H				
L	X	High Z				

Simplified Block Diagram

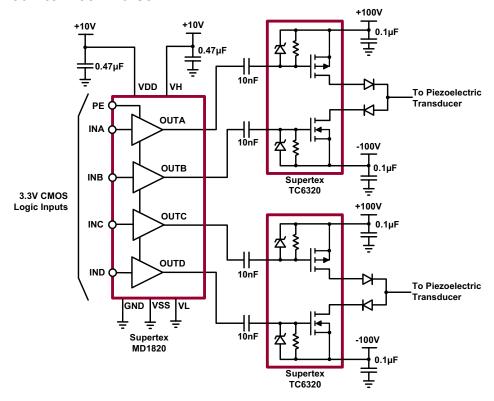


Detailed Block Diagram

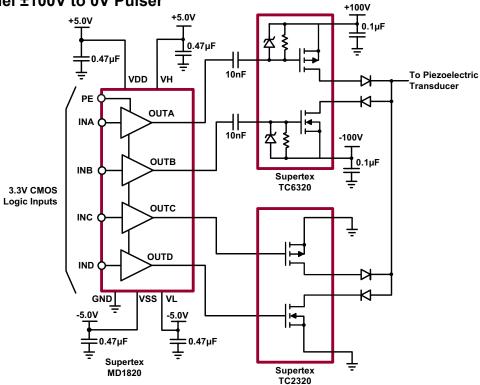


Typical Applications

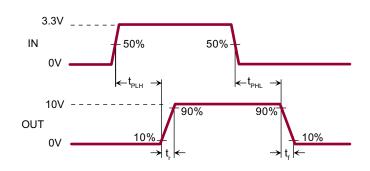
2-Channel +100V to -100V Pulser



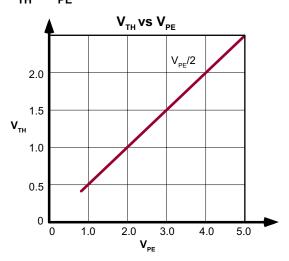
Single Channel ±100V to 0V Pulser



Timing Diagram



V_{TH} / V_{PF} Curve



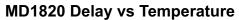
Application Information

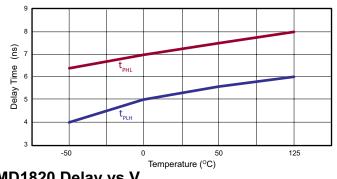
For proper operation of the MD1820, low inductance bypass capacitors should be used on the various supply pins. The GND pin should be connected to the logic ground. The INA, INB, INC, IND, and PE pins should be connected to a logic source with a swing of GND to PE, where PE is 1.8 to 5.0V. Good trace practices should be followed corresponding to the desired operating speed. The internal circuitry of the MD1820 is capable of operating up to 100MHz, with the primary speed limitation being the loading effects of the load capacitance. Because of this speed and the high transient currents that result with capacitive loads, the bypass capacitors should be as close to the chip pins as possible. Unless the load specifically requires bipolar drive, the VSS and VL pins should have low inductance feed-through connections directly to a ground plane. If these voltages are not zero, then they need bypass capacitors in a manner similar to the positive power supplies. The power connection VDD should have a ceramic bypass capacitor to the ground plane with short leads and decoupling components to prevent resonance in the powerleads.

The voltages of VH and VL decide the output signal levels. These two pins can draw fast transient currents of up to 2.0A, so they should be provided with an appropriate bypass

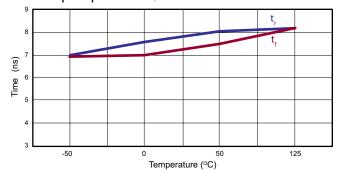
capacitor located next to the chip pins. A ceramic capacitor of up to 1.0µF may be appropriate, with a series ferrite bead to prevent resonance in the power supply lead coming to the capacitor. Pay particular attention to minimizing trace lengths, current loop area and using sufficient trace width to reduce inductance. Surface mount components are highly recommended. Since the output impedance of this driver is very low, in some cases it may be desirable to add a small series resistance in series with the output signal to obtain better waveform transitions at the load terminals. This will of course reduce the output voltage slew rate at the terminals of a capacitive load.

Pay particular attention that parasitic couplings are minimized from the output to the input signal terminals. The parasitic feedback may cause oscillations or spurious waveform shapes on the edges of signal transitions. Since the input operates with signals down to 1.8V even small coupled voltages may cause problems. Use of a solid ground plane and good power and signal layout practices will prevent this problem. Be careful that a circulating ground return current from a capacitive load cannot react with common inductance to cause noise voltages in the input logic circuitry.

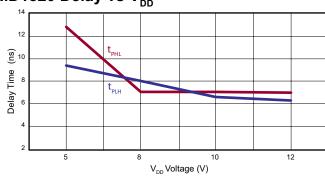




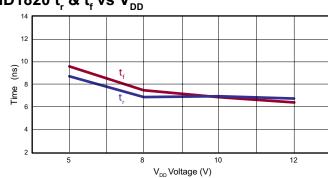
MD1820 t_{r} & t_{f} vs Temperature







MD1820 \mathbf{t}_{r} & \mathbf{t}_{f} vs \mathbf{V}_{DD}

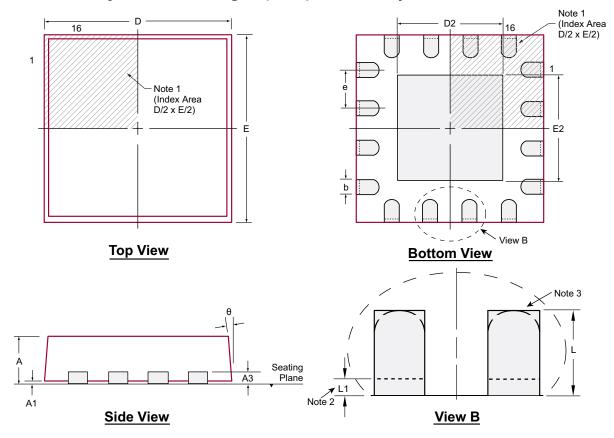


Pin Description

Pin#	Function	Description				
1	INB	Logic input.				
2	VDD	High side supply voltage.				
3	VSS	Low side supply voltage. VSS is also connected to the IC substrate. It is required to connect to the most negative potential of voltage supplies.				
4	INC	Logic input				
5	IND	Logic input.				
6	GND	Logic input ground reference.				
7	VL	Supply voltage for N-channel output stage.				
8	OUTC	Nutrout delicare				
9	OUTD	Output drivers				
10, 11	VH	Supply voltage for P-channel output stage.				
12	OUTA	Output delicare				
13	OUTB	Output drivers				
14	VL	Supply voltage for N-channel output stage.				
15	PE	Power enable logic input. When PE is high, sets the input logic threshold. When PE is low, all outputs are at default state (see truth table) and IC in standby mode.				
16	INA	Logic input.				
S	Substrate	The IC substrate is internally connected to the thermal pad. Thermal pad and VSS must be connected externally.				

16-Lead QFN Package Outline (K6)

3.00x3.00mm body, 1.00mm height (max), 0.50mm pitch



Notes:

- 1. A Pin 1 identifier must be located in the index area indicated. The Pin 1 identifier can be: a molded mark/identifier; an embedded metal marker; or a printed indicator.
- 2. Depending on the method of manufacturing, a maximum of 0.15mm pullback (L1) may be present.
- 3. The inner tip of the lead may be either rounded or square.

Symb	ol	Α	A1	А3	b	D	D2	Е	E2	е	L	L1	θ
	MIN	0.80	0.00		0.18	2.85*	1.50	2.85*	1.50		0.20†	0.00	0°
Dimension (mm)	NOM	0.90	0.02	0.20 REF	0.25	3.00	1.65	3.00	1.65	0.50 BSC	0.30†	-	-
(11111)	MAX	1.00	0.05		0.30	3.15*	1.80	3.15*	1.80		0.45	0.15	14º

JEDEC Registration MO-220, Variation VEED-4, Issue K, June 2006.

Drawings not to scale.

Supertex Doc.#: DSPD-16QFNK63X3P050, Version A092909.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to http://www.supertex.com/packaging.html.)

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^{*} This dimension is not specified in the JEDEC drawing.

[†] This dimension differs from the JEDEC drawing.